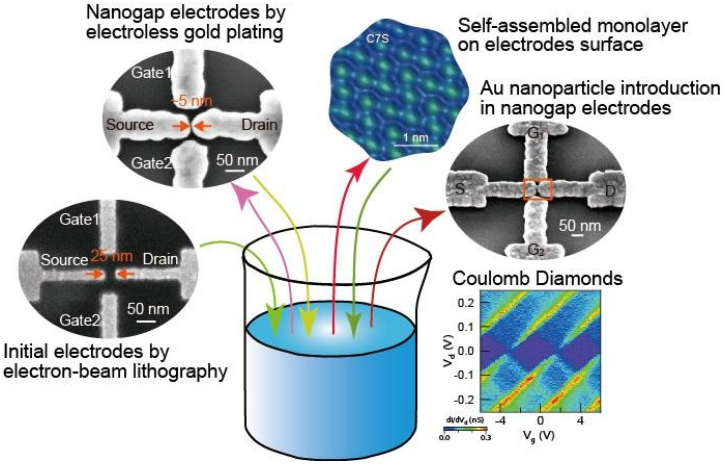
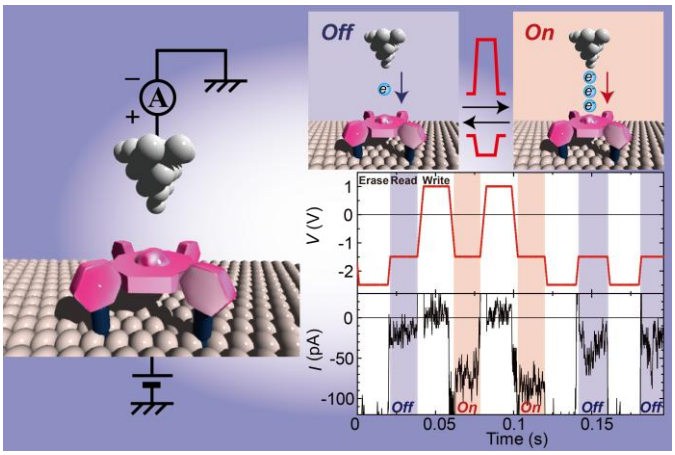
Molecular devices and nanoparticle devices by utilizing bottom-up processes

Bottom-up electronics enables us to fabricate chemically assembled single-electron devices and molecular devices with high sub-nm precision by dipping a sample into solutions. We have established the electroless plating process for nanogap electrodes with 5 nm or less gap separation at sub-nm scale precision. We have demonstrated the Coulomb blockade phenomena on a gold nanoparticle at room temperature by scanning tunneling microscopy (STM) and scanning tunneling spectroscopy (STS). By using these nanogap electrodes and the nanoparticle, we have demonstrated the exclusive or (XOR) operation on the double side-gate single-electron transistors. Our goal is to demonstrate the solid-state single-electron devices and molecular devices operations at room temperature by utilizing the chemical assembling of nanoparticles, functional molecules, and electroless plated nanogap electrodes.



Chemically assembled single-electron transistor and Coulomb diamond characteristic.



Room temperature single-molecular memory